

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	6.2	A
		T <sub>A</sub> = +70°C		4.9	
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	44	A
Maximum Body Diode Forward Current (Note 6)			I <sub>S</sub>	1.5	A
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	17.5	A
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	15.2	mJ

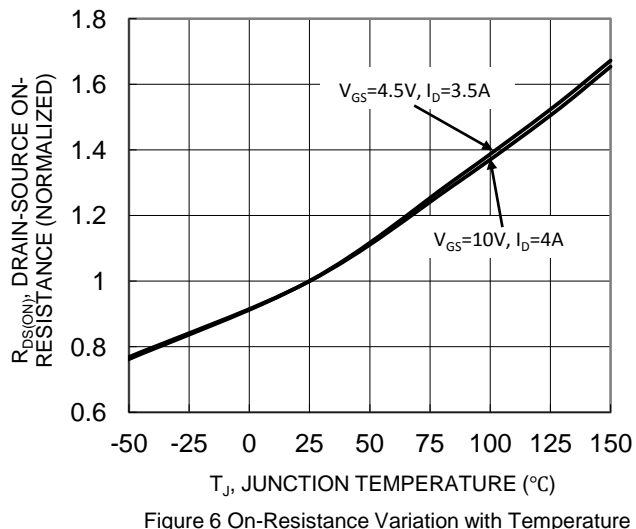
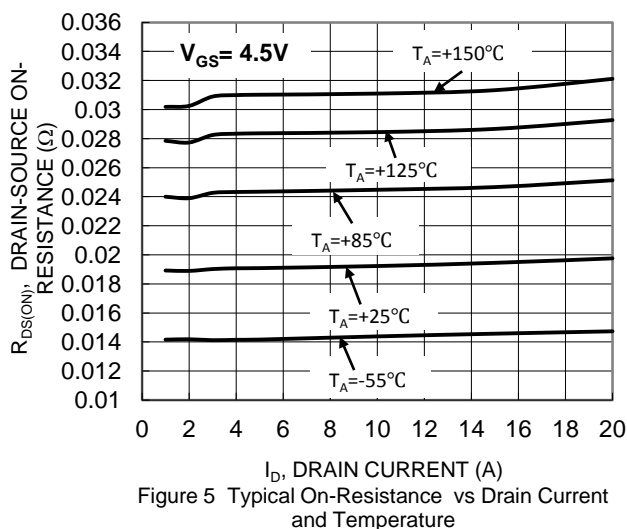
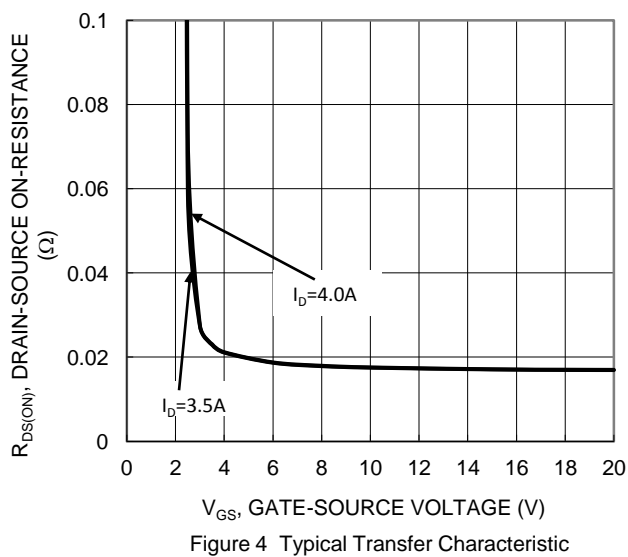
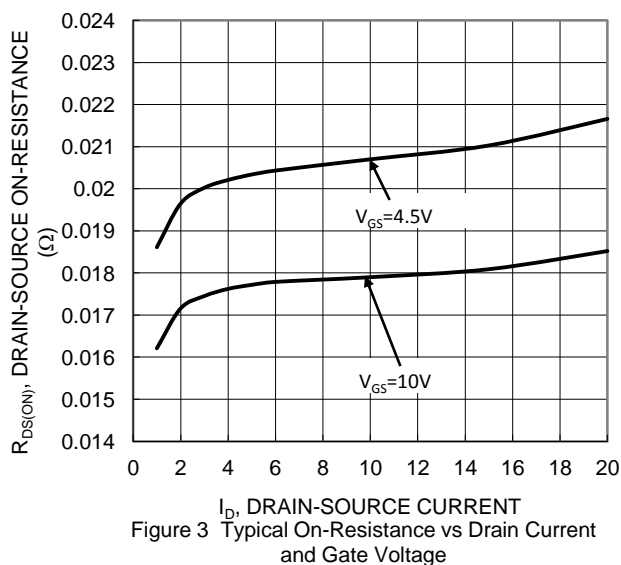
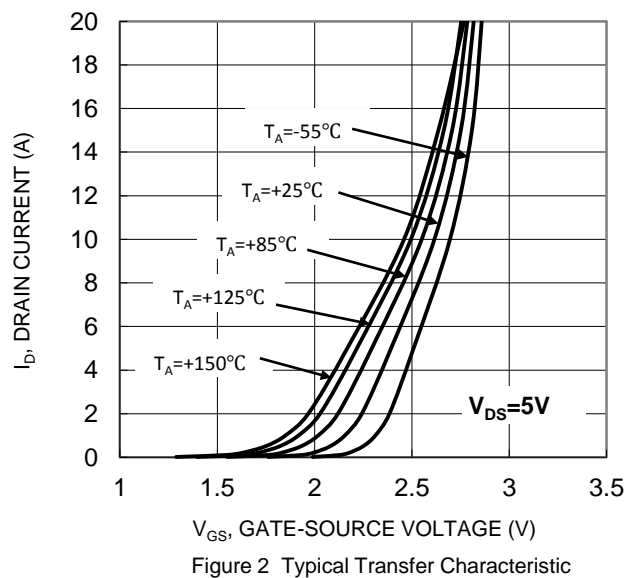
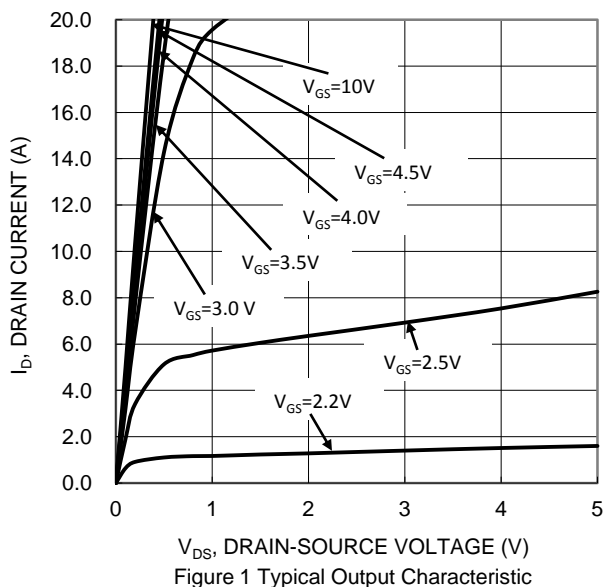
**Thermal Characteristics**

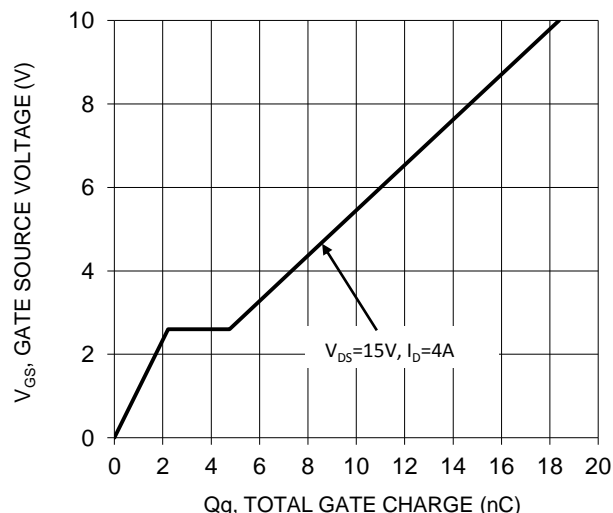
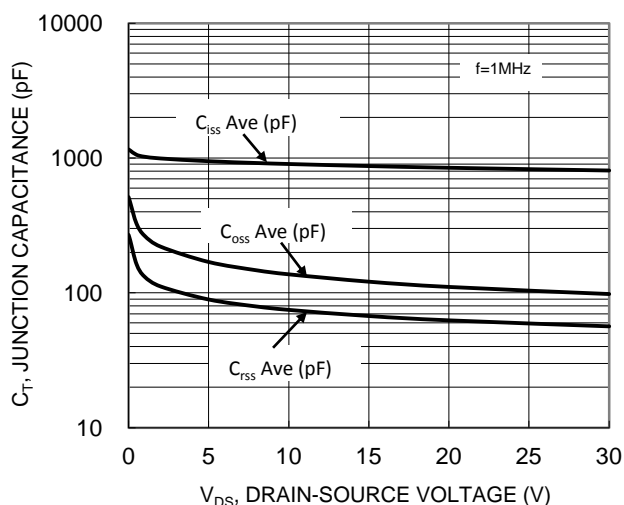
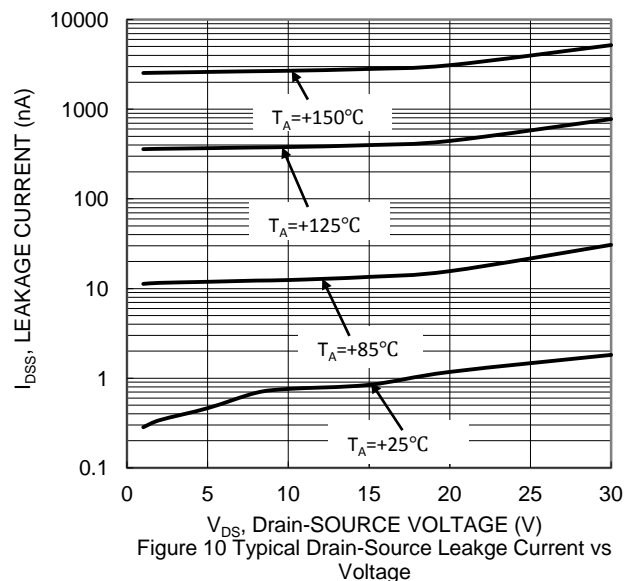
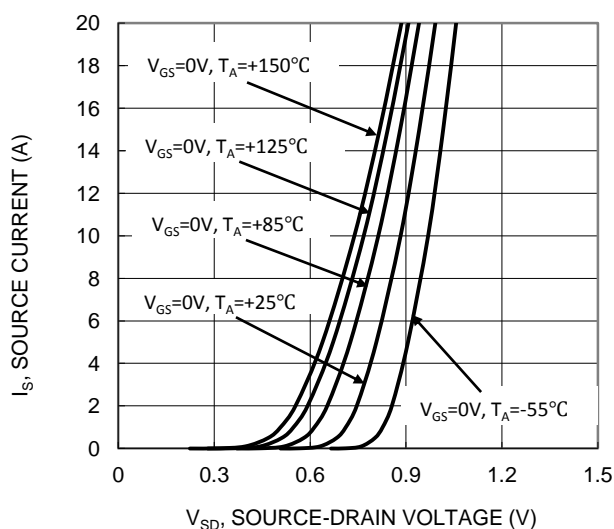
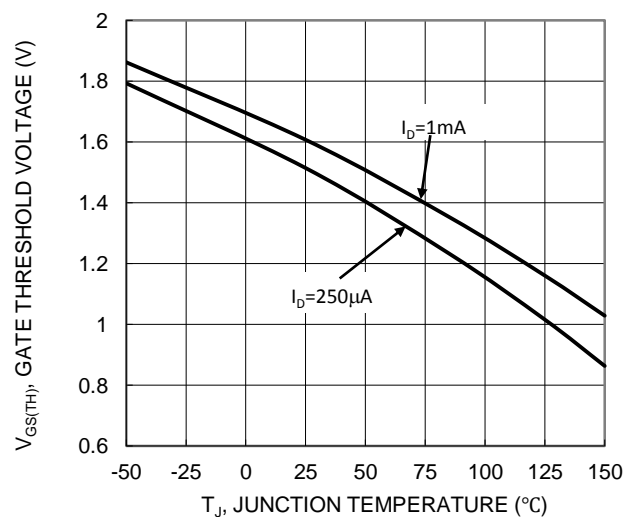
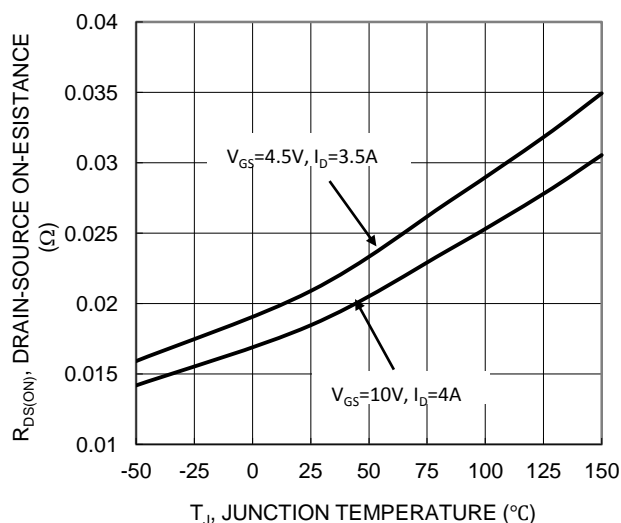
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.9	W
	T <sub>A</sub> = +70°C		0.6	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R <sub>θJA</sub>	144	°C/W
	t < 10s		103	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.3	W
	T <sub>A</sub> = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R <sub>θJA</sub>	97	°C/W
	t < 10s		70	
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	24	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

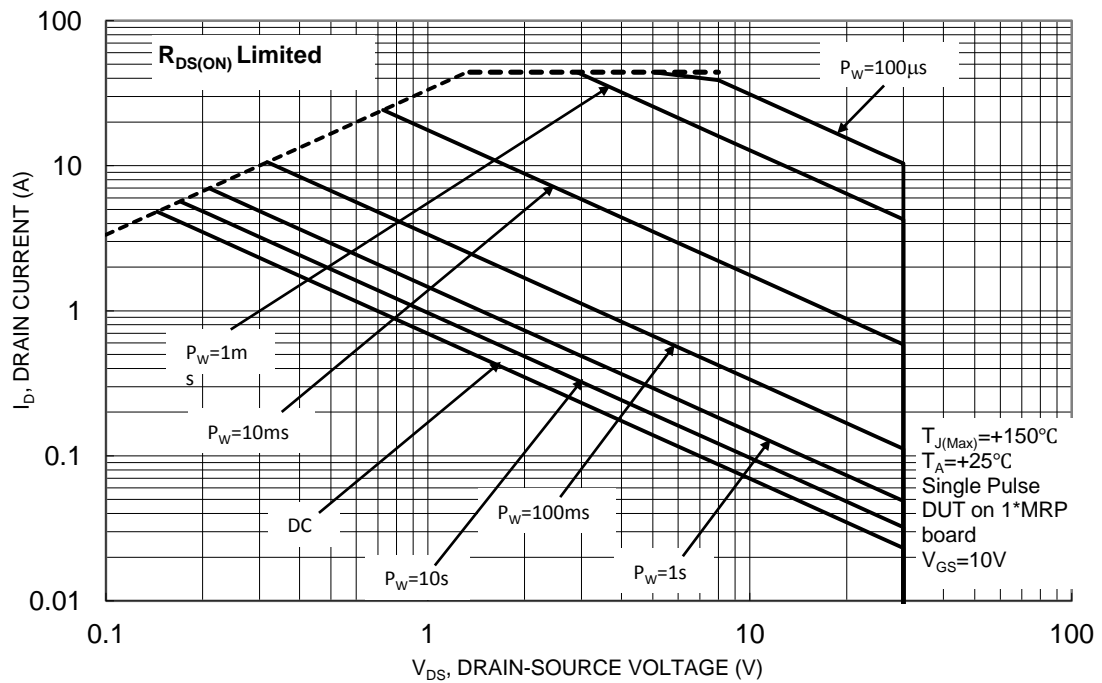
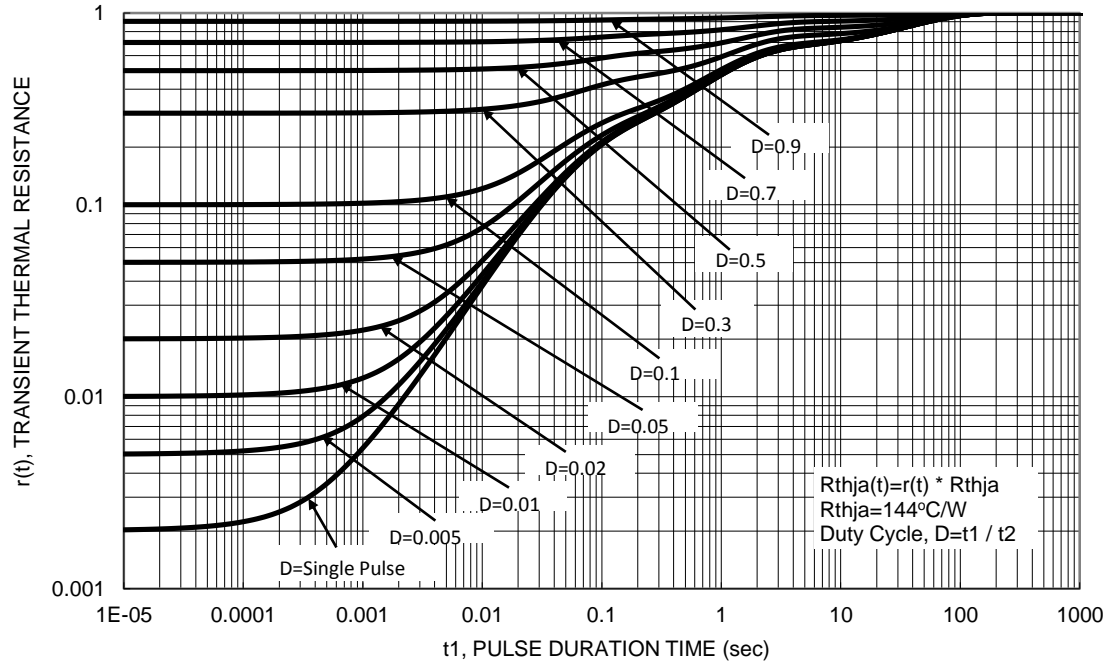
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8	—	1.8	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	25	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.0A
		—	—	28		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.5A
		—	—	68		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 2.5A
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	—	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	873	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	121	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	67	—	pF	
Gate Resistance	R <sub>g</sub>	—	77	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	18.4	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 4A
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	8.3	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	2.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	2.5	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	17	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 15Ω, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>r</sub>	—	18	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	231	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	70	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

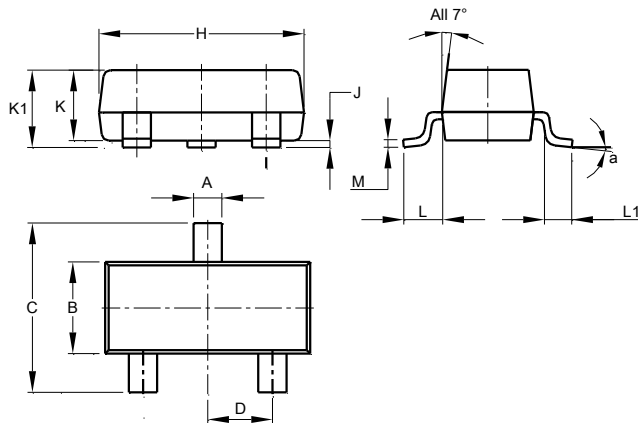






## Package Outline Dimensions

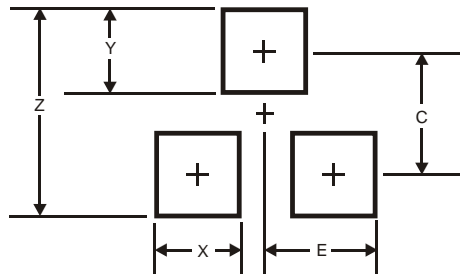
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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